

N-channel LFPAK 80 V 11 m $\Omega$  standard level MOSFET

Rev. 02 — 28 October 2010

Product data sheet

### 1. Product profile

### 1.1 General description

Standard level N-channel MOSFET in LFPAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

### 1.2 Features and benefits

- Advanced TrenchMOS provides low RDSon and low gate charge
- High efficiency gains in switching power converters

### 1.3 Applications

- DC-to-DC converters
- Lithium-ion battery protection
- Load switching

### Improved mechanical and thermal characteristics

- LFPAK provides maximum power density in a Power SO8 package
- Motor control
- Server power supplies

### **1.4 Quick reference data**

Table 1.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	-	80	V
I <sub>D</sub>	drain current	$T_{mb} = 25 \text{ °C}; V_{GS} = 10 \text{ V};$ see <u>Figure 1</u>	-	-	67	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	-	117	W
Tj	junction temperature		-55	-	175	°C
Static ch	aracteristics					
$R_{DSon}$	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 100 °C; see <u>Figure 12</u>	-	-	18	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ T <sub>j</sub> = 25 °C; see Figure 12;	-	8.6	11	mΩ

see Figure 13



### N-channel LFPAK 80 V 11 mΩ standard level MOSFET

Table 1.	Quick reference datac	ontinued				
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Dynamic	characteristics					
$Q_{GD}$	gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$	-	11	-	nC
Q <sub>G(tot)</sub>	total gate charge	V <sub>DS</sub> = 40 V; see <u>Figure 14;</u> see <u>Figure 15</u>	-	45	-	nC
Avalanch	e ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$ \begin{split} V_{GS} &= 10 \ V; \ T_{j(init)} = 25 \ ^{\circ}C; \\ I_{D} &= 67 \ A; \ V_{sup} \leq 80 \ V; \\ R_{GS} &= 50 \ \Omega; \ unclamped \end{split} $	-	-	121	mJ

## 2. Pinning information

Table 2.	Pinning	g information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		_
2	S	source	mb	
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain		mbb076 S
			SOT669 (LFPAK)	

### 3. Ordering information

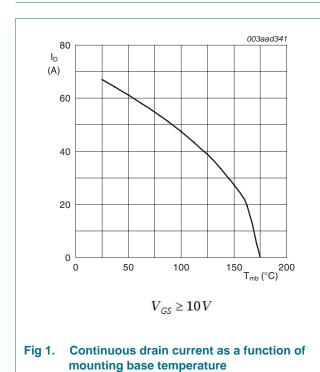
Table 3.	Ordering in	formation		
Type numb	er	Package		
		Name	Description	Version
PSMN011-8	OYS	LFPAK	plastic single-ended surface-mounted package (LFPAK); 4 leads	SOT669

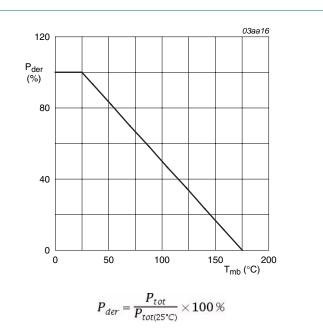
### 4. Limiting values

#### Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	80	V
V <sub>DGR</sub>	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$	-	80	V
V <sub>GS</sub>	gate-source voltage		-20	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; see <u>Figure 1</u>	-	47	А
		$V_{GS}$ = 10 V; $T_{mb}$ = 25 °C; see <u>Figure 1</u>	-	67	А
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$ ; see Figure 3	-	266	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	117	W
T <sub>stg</sub>	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature		-	260	°C
Source-drai	n diode				
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	-	67	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$	-	266	А
Avalanche r	uggedness				
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 67 A; $V_{sup} \le 80$ V; $R_{GS}$ = 50 $\Omega$ ; unclamped	-	121	mJ

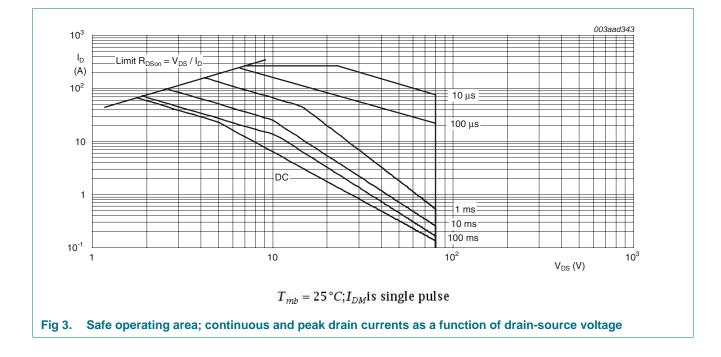






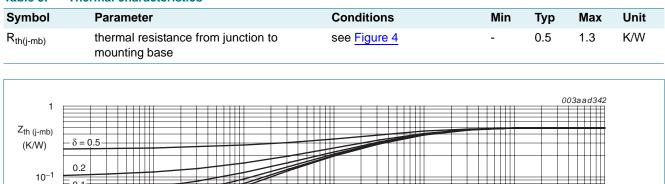
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# **PSMN011-80YS**



#### **Thermal characteristics** 5.

10<sup>-5</sup>



10-2

10-1

tp (s)

#### Table 5. **Thermal characteristics**

Transient thermal impedance from junction to mounting base as a function of pulse duration; typical Fig 4. values

10-4

10<sup>\_3</sup>

0.1

0.05 0.02

single shot

10-2

10<sup>-3</sup>

1-6

### 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = -55 °C	73	-	-	V
	voltage	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$	80	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 175 °C; see <u>Figure 10</u>	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ see <u>Figure 10</u>	-	-	4.6	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 11</u> ; see <u>Figure 10</u>	2	3	4	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 80 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	1	μA
		$V_{DS} = 80 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ °C}$	-	-	100	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = -20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	100	nA
		$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nA
R <sub>DSon</sub> drain-source on-state resistance	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 175 °C; see <u>Figure 12</u>	-	19	26	mΩ
		$V_{GS}$ = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 100 °C; see Figure 12	-	-	18	mΩ
		$V_{GS}$ = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; see Figure 12; see Figure 13	-	8.6	11	mΩ
R <sub>G</sub>	internal gate resistance (AC)	f = 1 MHz	-	0.7	-	Ω
Dynamic cha	aracteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	38	-	nC
		$I_D = 25 \text{ A}; V_{DS} = 40 \text{ V}; V_{GS} = 10 \text{ V};$	-	45	-	nC
Q <sub>GS</sub>	gate-source charge	see Figure 14; see Figure 15	-	13	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate-source charge	$I_D = 25 \text{ A}; V_{DS} = 40 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 14	-	8	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate-source charge		-	5	-	nC
Q <sub>GD</sub>	gate-drain charge	$I_D = 25 \text{ A}; V_{DS} = 40 \text{ V}; V_{GS} = 10 \text{ V};$ see <u>Figure 14</u> ; see <u>Figure 15</u>	-	11	-	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	$I_D = 25 \text{ A}; V_{DS} = 40 \text{ V}; \text{ see } \frac{\text{Figure } 14}{\text{See } \frac{\text{Figure } 15}{\text{See } \frac{1}{2}}$	-	4.9	-	V
C <sub>iss</sub>	input capacitance	$V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	2800	-	pF
C <sub>oss</sub>	output capacitance	$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 16}{100}$	-	270	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	146	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 40 V; $R_{L}$ = 1.6 Ω; $V_{GS}$ = 10 V;	-	23	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 4.7 \ \Omega$	-	20	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	40	-	ns
t <sub>f</sub>	fall time		-	12	-	ns

Symbol

Source-drain diode

# **PSMN011-80YS**

Тур

Unit

Max

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Min

SD	source-drain voltage	I <sub>S</sub> = 25 A; V <sub>C</sub> see <u>Figure 1</u>	<sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C <u>7</u>	;; -	0.8	1	.2	V
	reverse recovery time		<sub>S</sub> /dt = 100 A/µs;	-	54	-		ns
r	recovered charge	V <sub>GS</sub> = 0 V; V	′ <sub>DS</sub> = 40 V	-	98	-		nC
100 I <sub>D</sub> (A) 80		03aad311 5.5-	100 I <sub>D</sub> (A) 80			003a	ad333	
60			60			#		
40		5	40					
20	V <sub>GS</sub> (V	) = 4.5	20	Tj =	175 °C	$-T_j = 25$	5 °C-	
0	) 1 2 V	<sub>DS</sub> (V) <sup>3</sup>	0	2	4	V <sub>GS</sub> (\	6	
	$T_j = 25 ^{\circ}C$ Output characteristics: drain cur unction of drain-source voltage;	rent as a		$V_{DS} > I_{I}$ r characteria of gate-sou				
fı	$T_j = 25 ^{\circ}C$ Output characteristics: drain cur unction of drain-source voltage;	rent as a typical values	function	r characteri	stics: drai	ge; ty	pical v	
	$T_j = 25 ^{\circ}C$ Output characteristics: drain cur unction of drain-source voltage;	rent as a		r characteri	stics: drai	ge; ty	ad337	
100 g <sub>fs</sub> (S)	$T_j = 25 ^{\circ}C$ Output characteristics: drain cur unction of drain-source voltage;	rent as a typical values	4000 C (pF)	r characteri	stics: drai	<b>ge; ty</b>	ad337	
100 9 <sub>fs</sub> (S) 80	$T_j = 25 ^{\circ}C$ Output characteristics: drain cur unction of drain-source voltage;	rent as a typical values	4000 C (pF) 3500	r characteri	stics: drai	<b>ge; ty</b>	ad337 s	
100 g <sub>fs</sub> (S) 80 60	$T_j = 25 ^{\circ}C$ Output characteristics: drain cur unction of drain-source voltage;	rent as a typical values	function 4000 C (pF) 3500 3000 2500	r characteri	stics: drai	9e; ty 003a C <sub>is</sub>	ad337 s	
100 g <sub>fs</sub> (S) 80 60 40	$T_j = 25 ^{\circ}C$	rent as a typical values	function 4000 C (pF) 3500 2500 2000 1500 1000	r characteri	stics: drai	9e; ty 003a C <sub>is</sub>	ad337	
ft 100 g <sub>fs</sub> (S) 80 60 40 20	$T_j = 25 ^{\circ}C$	rent as a typical values	function 4000 C (pF) 3500 2500 2000 1500 1000	r characteria of gate-sou	stics: drai	20 VGS	ad337	

Conditions

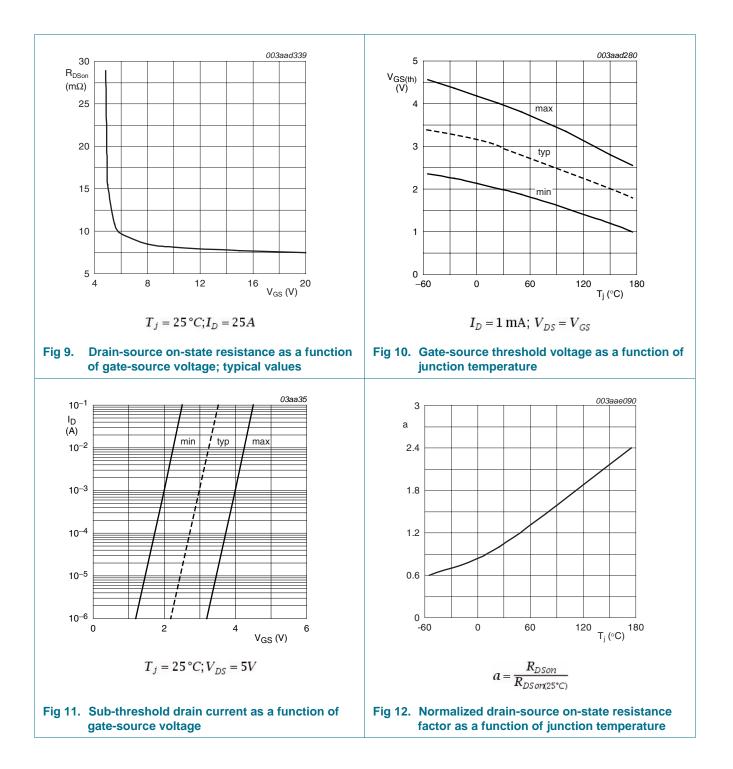
#### Table 6. Characteristics ...continued

Parameter

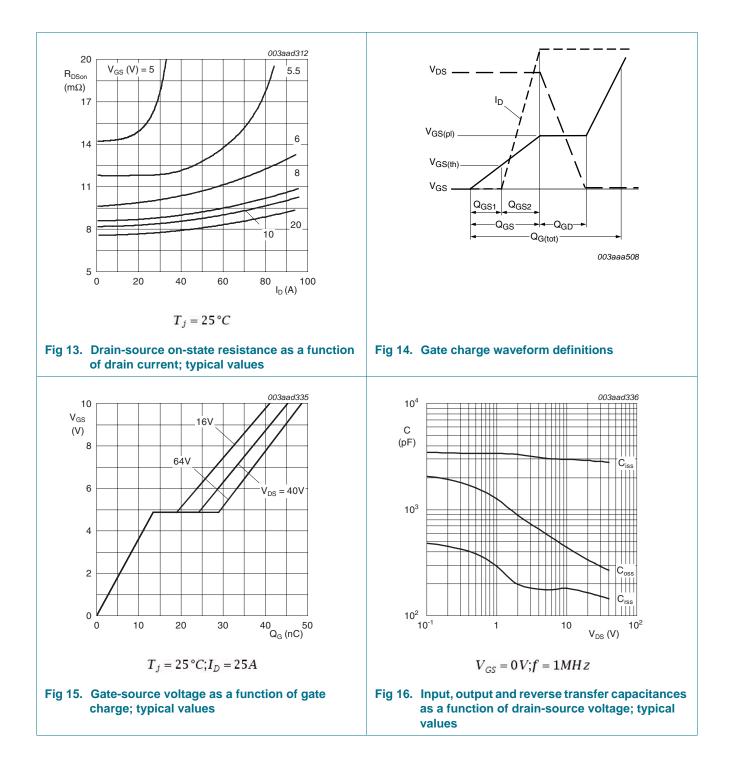
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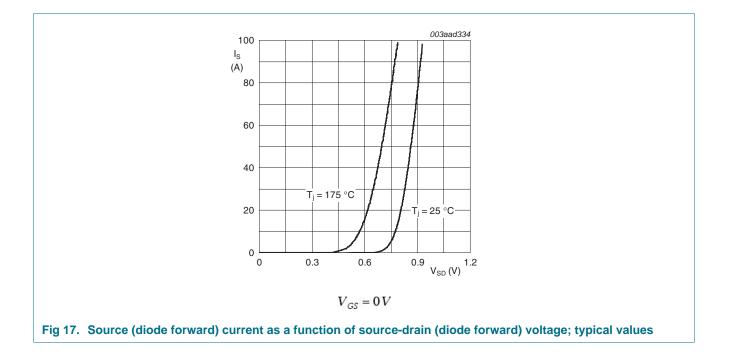
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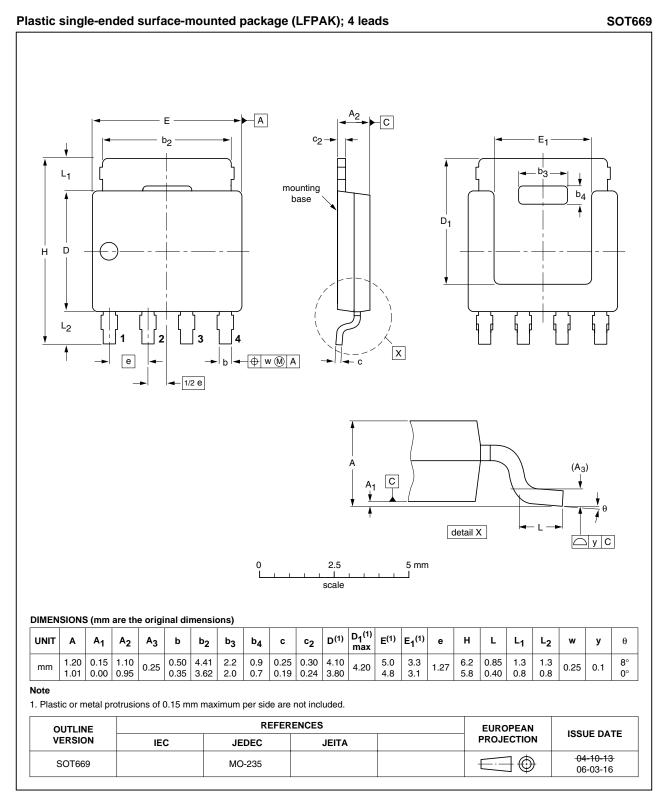


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### 7. Package outline



#### Fig 18. Package outline SOT669 (LFPAK)

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## 8. Revision history

Table 7. Revision h	nistory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN011-80YS v.2	20101028	Product data sheet	-	PSMN011-80YS v.1
Modifications:	<ul> <li>Status change</li> </ul>	d from objective to product.		
	<ul> <li>Various chang</li> </ul>	es to content.		
PSMN011-80YS v.1	20100226	Objective data sheet	-	-

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### 9. Legal information

### 9.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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